## TOSHIBA

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

### RN2961FE,RN2962FE,RN2963FE RN2964FE,RN2965FE,RN2966FE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- Two devices are incorporated into an Extreme-Super-Mini (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN1961FE~RN1966FE

#### **Equivalent Circuit and Bias Resistor Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN2961FE	4.7	4.7
RN2962FE	10	10
RN2963FE	22	22
RN2964FE	47	47
RN2965FE	2.2	47
RN2966FE	4.7	47



Weight: g (typ.)

#### Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage	RN2961FE~2966FE	V <sub>CBO</sub>	-50	V	
Collector-emitter voltage		V <sub>CEO</sub> –50		V	
Emitter-base voltage	RN2961FE~2964FE	V <sub>EBO</sub>	-10	V	
	RN2965FE, 2966FE	▲EBO	-5		
Collector current		Ι <sub>C</sub>	-100	mA	
Collector power dissipation	RN2961FE~2966FE	P <sub>C</sub> (Note)	100	mW	
Junction temperature	RIN2901FE~2900FE	Тj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

# Equivalent Circuit (top view)



Note: Total rating

Unit: mm

## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2961FE~2966FE	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$	_		-100	nA
		ICEO	$V_{CE} = -50 \text{ V}, \text{ I}_{B} = 0$	_		-500	ΠA
Emitter cut-off current	RN2961FE	Іево	$V_{EB} = -10 \text{ V}, \text{ I}_{C} = 0$	-0.82		-1.52	mA
	RN2962FE			-0.38		-0.71	
	RN2963FE			-0.17		-0.33	
	RN2964FE			-0.082		-0.15	
	RN2965FE			-0.078		-0.145	
	RN2966FE		$V_{EB} = -5 V, I_C = 0$	-0.074		-0.138	
	RN2961FE		V <sub>CE</sub> = -5 V, I <sub>C</sub> = -10 mA	30			
	RN2962FE			50	_	_	
DC current gain	RN2963FE			70			
	RN2964FE	h <sub>FE</sub>		80			
	RN2965FE			80			
	RN2966FE			80		_	
Collector-emitter saturation voltage	RN2961FE~2966FE	V <sub>CE (sat)</sub>	$I_C = -5 \text{ mA},$ $I_B = -0.25 \text{ mA}$	_	-0.1	-0.3	V
Input voltage (ON)	RN2961FE	VI (ON)	$V_{CE} = -0.2 V,$ $I_{C} = -5 mA$	-1.1		-2.0	V
	RN2962FE			-1.2		-2.4	
	RN2963FE			-1.3		-3.0	
	RN2964FE			-1.5		-5.0	
	RN2965FE			-0.6		-1.1	
	RN2966FE			-0.7		-1.3	
Input voltage (OFF)	RN2961FE~2964FE	V <sub>I (OFF)</sub>	$V_{CE} = -5 \text{ V},$ $I_{C} = -0.1 \text{ mA}$	-1.0		-1.5	v
	RN2965FE, 2966FE			-0.5	_	-0.8	
Transition frequency	RN2961FE~2966FE	f <sub>T</sub>	$V_{CE} = -10 \text{ V},$ $I_{C} = -5 \text{ mA}$	—	200	_	MHz
Collector output capacitance	RN2961FE~2966FE	C <sub>ob</sub>	$\label{eq:VCB} \begin{array}{l} V_{CB} = -10 \ V, \ I_E = 0, \\ f = 1 \ MHz \end{array}$	_	3	6	pF
Input resistor	RN2961FE	R1		3.29	4.7	6.11	kΩ
	RN2962FE			7	10	13	
	RN2963FE			15.4	22	28.6	
	RN2964FE			32.9	47	61.1	
	RN2965FE			1.54	2.2	2.86	
	RN2966FE			3.29	4.7	6.11	
Resistor ratio	RN2961FE~2964FE	R1/R2	_	0.9	1.0	1.1	-
	RN2965FE			0.0421	0.0468	0.0515	
	RN2966FE			0.09	0.1	0.11	

Type Name	Marking
RN2961FE	Type name Y Y A
RN2962FE	Type name Y Y B
RN2963FE	Type name Y Ý C
RN2964FE	Type name Y Y D •
RN2965FE	Type name Y Y E
RN2966FE	Type name Y Ý F

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